

## Amendments to the Claims

**1. (Currently amended)** A silicon epitaxial wafer ~~having an excellent gettering capability in the entire radial direction thereof~~, comprising a silicon single crystal substrate and an epitaxial layer grown on a surface of the silicon single crystal substrate, wherein the silicon single crystal substrate after epitaxial growth has a density of oxide precipitates which are detectable in the interior of a the silicon single crystal substrate after epitaxial growth is of  $1 \times 10^9/\text{cm}^3$  or higher at any position in the radial direction, and wherein the silicon single crystal substrate prior to epitaxial growth is heat treated in an oxidizing atmosphere so that Grown-in precipitation nuclei are grown in the silicon single crystal but stacking faults in the form of a ring are not generated in the silicon single crystal substrate.

**2. (Cancelled)**

**3. (Previously presented)** The silicon epitaxial wafer according to claim 1, wherein the silicon single crystal substrate prior to the epitaxial growth is a boron-doped substrate having resistivity of  $0.1 \Omega\cdot\text{cm}$  or lower.

**4. (Currently amended)** A process for manufacturing a silicon epitaxial wafer ~~having an excellent gettering capability in the entire substrate~~ comprising the steps of:

heat treating a silicon single crystal substrate in an oxidizing atmosphere for a growing to grow Grown-in precipitation nuclei in the silicon single crystal substrate; and thereafter,

performing epitaxial growth on the substrate,

wherein ~~there is used as the substrate a silicon single crystal wafer which has Grown-in precipitation nuclei formed in a growth step for silicon single crystal, and in which~~ stacking faults in the form of a ring are not generated in a the silicon single crystal substrate during the heat treatment in an oxidizing atmosphere.

**5. (Original)** The process for manufacturing a silicon epitaxial wafer according to claim 4, wherein the substrate is a boron-doped substrate having resistivity of  $0.1 \Omega\cdot\text{cm}$  or lower.

6. **Cancelled**